Metalens-integrated compact imaging devices for wide-field microscopy

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Abstract. Metasurfaces have demonstrated unprecedented capabilities in manipulating light with ultrathin and flat architectures. Although great progress has been made in the metasurface designs and function demonstrations, most metalenses still only work as a substitution of conventional lenses in optical settings, whose integration advantage is rarely manifested. We propose a highly integrated imaging device with silicon metalenses directly mounted on a complementary metal oxide semiconductor image sensor, whose working distance is in hundreds of micrometers. The imaging performances including resolution, signal-to-noise ratio, and field of view (FOV) are investigated. Moreover, we develop a metalens array with polarization-multiplexed dual-phase design for a wide-field microscopic imaging. This approach remarkably expands the FOV without reducing the resolution, which promises a non-limited space-bandwidth product imaging for wide-field microscopy. As a result, we demonstrate a centimeter-scale prototype for microscopic imaging, showing uniqueness of meta-design for compact integration.

Keywords: metalens; compact imaging device; polarization multiplexing; wide-field microscopy.

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1 Introduction

Current imaging technology has been well developed by versatile strategies for outstanding performances in high resolution, high image quality, and broad wavelength band. Most of these techniques are established on the basis of mature refractive or reflective optical elements, such as lenses, internal reflection mirrors, etc., which result in optical systems that are bulky, heavy, and inconvenient for portability. However, more compact, light, and stable optical systems are the ever-growing requirement of modern applications. Recent advances in computational imaging (including the lensless and scattering medium imaging) have shown a successful route to reduce the complexity of the optical system by discarding the refractive lenses.1,2 Nevertheless, they are not a real physical image, and the image quality strongly relies on the post-processing algorithms, such as iterative phase recovery algorithm,3,4 compressive sensing,5,6 and Fourier ptychography.7,8 It inevitably requires computational resources that are time consuming and sometimes needs particular prior knowledge for imaging reconstruction.

Benefiting from the development of nanofabrication technology, the metasurface as a new breakthrough of optical design has demonstrated tremendous capabilities in manipulating light by subwavelength unit cells,9–12 and fascinating applications with the low loss dielectric metasurfaces have been revealed.13–16 Among these applications, the metalens is one of the most promising candidates for upgrading current optical systems. During the past several years, exciting progress concerning the imaging performance of the metalens has been made, including improved efficiency,17,18 broadband achromaticism,19–21 broadened field-of-view (FOV),22,23 polarization functionalities,24,25 etc., which indicates a closer step toward real
showing their uniqueness for integration.21,28
almost the same role in conventional optical settings without
play imaging performance. In most previous works, metalenses act
only as substitutes for conventional refractive lenses and play
almost the same role in conventional optical settings without
showing their uniqueness for integration.21,26,27

In this work, we directly integrate the metalenses onto the
complementary metal oxide semiconductor (CMOS) image
sensor to show the major advantage of the flat metalens. The
metalenses were manufactured in amorphous silicon (α-Si)
nano-posts designed by the geometric Pancharatnam–Berry
(PB) phase on a SiO2 substrate, where the Si material was used
for potential compatibility to full CMOS-based devices. After
careful characterization of the imaging qualities with respect
to the resolution, signal-to-noise ratio (SNR), FOV, and so on,
we show the capability of this metalens-integrated imaging
device (MIID) for spectral focal tuning31 due to the large
dispersion. It breaks the limitation of lens-free shadow imaging
that cannot resolve the depth-of-field (DOF) of the object.32

More importantly, we develop a metalens array to cover a
wide area of CMOS image sensors for a wide-field imaging.
To eliminate the blind areas in multiple-images-stitching,
here, we utilize a polarization-multiplexed dual-phase (PMDP)
design (with respect to two circular polarizations) to access
two sets of lenses with complementary image areas. A full
stitched wide-field image is completed only by switching
the polarizer without any mechanical movement. As a re-
result, we achieved high-resolution images (∼1.74 μm almost
limited by image sensor pixel) with a millimeter-scale image
area (expandable to whole centimeter-scale CMOS sensor),
which was ultimately implemented in a ∼3-cm size device
prototype. This ultra-compact microscope system promises
more exciting applications of metalens in high resolution, large
FOV, and tunable DOF imaging.

2 Device Architecture and Fabrication

Figure 1(a) shows the schematics of imaging setup for our
MIID. An optically clear adhesive (OCA) tape (Tesa, 69402)
is used to transfer and fix the metalens on the CMOS image
sensor ( Imaging source, DMM 27UJ003-ML, pixel size:
1.67 μm × 1.67 μm ) with proper thickness for imaging distance
( the distance between the CMOS image sensor and metalens )
in our experiment. Here, the OCA is employed for its colorless
transparency with high transmittance (>90%) in the visible
and near-infrared ranges, which is widely used in optoelectronic
deVICES. We also take OCA tape as the spacer medium of inte-
gration for the well-defined stationary thickness. The detailed
metalens integration process is further described in Sec. S1
of the Supplementary Material. With skillful operation, the in-
tegration deviation is very small, and the distortion caused by
lens tilting can be handled. Once the metalens is mounted on
the CMOS image sensor, the imaging distance is fixed, and a clear
image can be acquired by tuning the object distance v ( the dis-
tance between metalens and object ) with the translation stage.
Figure 1(b) shows the photograph of the highly compact MIID
(here, v = 500 μm). It should be noted that, due to the complex
medium layers in both image space and object space of the meta-
len, the parameters ( u, v ) here are effective ones containing the
influence of the medium. We first measured the effective imaging
distance and take it as constant in our theoretical design.
A white-light source of a halogen lamp with color filters was
employed for incoherent monochromatic illumination. The meta-
len is designed as an aplanatic lens to eliminate on-axis aber-
rations for the 4f imaging scheme ( u = v = 2f ) with a phase profile of11

\[
\varphi = \frac{4\pi}{\lambda} \left( 2f - \sqrt{R^2 + 4f^2} \right). \tag{1}
\]

where \( \lambda \) is the designed working wavelength, f is the focal
length, and R is the radial coordinate. This required phase profile
is imparted via the geometric phase (i.e., PB phase), which is widely used in metasurface design. Here, we choose α-Si as our metalens material for its high refractive index (∼4.06), relatively low loss at long wavelengths in the visible (λ > 600 nm), and particularly its compatibility to the CMOS platform. A 200-μm-diameter metalens composed of nano-posts is fabricated in an 850-nm-thick α-Si film deposited on a 200-μm-thick fused silica substrate. The metalens is designed to work at a wavelength of 630 nm with NA ∼ 0.37 (diameter D = 200 μm, f = 250 μm). To avoid high-order diffractions, the rectangular nano-post units are designed with sizes of 80 nm × 200 nm in a height of 850 nm (equal to thickness of deposited Si film) and arranged in a square lattice with period of 400 nm. The simulated polarization conversion rate (PCR) is as high as ∼97.78% for the unit structure to guarantee high efficiency. The PCR is defined as |t_{cross}|^2/(|t_{cross}|^2 + |t_{co}|^2), where t_{cross} and t_{co} represent the complex transmission coefficients of cross-polarized and co-polarized light, respectively. The metalens is fabricated using standard electron-beam lithography and dry etching. The detailed fabrication process is described in Sec. S1 of the Supplementary Material. The optical microscope image and scanning electron microscope (SEM) image of the metalens are shown in Fig. 1(c), respectively.

3 Characterization of the Single Metalens Imaging

The 1951 United States Air Force (USAF) resolution test chart (Edmund, Positive 1951 USAF Hi-Resolution Target) is used as the imaging target. Figure 2(a) shows the image formed by MIID with a metalens of NA = 0.37 at imaging distance of 2f, with operating wavelength of 630 nm, revealing resolution of 1.74 μm (element 2, group 8), as shown in Fig. 2(c). The resolution of MIID is limited by the pixel size of the CMOS image sensor (1.67 μm) without image magnification. Figure 2(b) shows the image obtained with metalens of NA = 0.45 (D = 200 μm, f = 200 μm) at imaging distance v = 500 μm with operating wavelength of 630 nm. The resolution is 1.23 μm (element 5, group 8), as shown in Fig. 2(d), with image magnification of about 1.5. By careful observation, in Figs. 2(c) and
we find that the contrast of gray value of vertical lines is much weaker, which makes them hardly resolvable. It is due to the inequivalent CMOS pixels in two dimensions. Strictly speaking, our device only reaches the resolution of g8e2 (1.74 μm) and g8e5 (1.23 μm) in the y-dimension in equal-size (4f) and magnification image cases, respectively.

To get a compact imaging device, we did not add polarization analyzers between the metalens and the CMOS image sensor due to the limited space. The calculated high PCR also ensures the focus and imaging efficiency. To analyze the experimental imaging performances, we define SNR = 10 lg (Isignal/I\text{noise}), where I\text{signal} denotes the intensity of the signal that can be clearly resolved, such as element 1, group 8, and I\text{noise} denotes the standard deviation of the background noise intensity. For instance, Fig. 2(e) depicts the imaging data of USAF elements well under the resolution to evaluate the signal and noise [see the lines of element 1, group 8 in Fig. 2(a) in the left panel and lines of element 3, group 8 in Fig. 2(b) in the right panel]. To obtain an SNR as accurate as possible, we calculate SNR from multiple sets of signals and noises [Fig. 2(e)] and compute their average value as the calculated SNR. According to our experimental data, we get the SNR of about 19.89 dB in Fig. 2(a), which decreases to 9.23 dB in the 1.5× magnification case in Fig. 2(b). Moreover, the image quality of Fig. 2(a) appears much better than Fig. 2(b) due to the sharper image signals over the background, which is usually determined by the image contrast. Here, we define it as |(I_s - I_{bg})/(I_s + I_{bg})|, where I_s indicates the average minimum signal intensity, and I_{bg} indicates the average background intensity, as shown in Fig. 2(e). Then, we calculated the image contrasts for Figs. 2(a) and 2(b) with the data of 0.33 and 0.15, respectively, showing better imaging performance in contrast to the equal size image in the 4f system.

To get a systematic characterization of the imaging resolution by this MIID, a series of metalenses with different NAs on MIID were characterized at the 4f imaging scheme [see Fig. 2(f)]. The discrepancy between the measured resolution and theoretical value would possibly be due to the imperfection of metalens fabrication, the background noises, and pixel-size limited CMOS image sensor; more discussion is provided in Sec. S2 of the Supplementary Material. Moreover, the modulation transfer function (MTF) was obtained by the slanted-edge method, which shows good agreement with theoretical diffraction-limited MTF at low spatial frequency, as plotted in Fig. 2(g). The discrepancy between our measured MTF and the diffraction limit at high spatial frequency would also probably be attributed to the background noises and pixel-size-limited CMOS sensor as well.

Although the metalens mounted on CMOS image sensor leads to a fixed imaging distance, we can realize optical zoom easily by tuning the working wavelength according to the large dispersive metalens. Taking a designed metalens (focal length of 250 μm at λ = 630 nm) as an example, we obtained the images of USAF 1951 target (part of group 6) at λ = 560, 580, 600, 610, 620, and 630 nm with an imaging distance as constant at about 500 μm [see Fig. 3(a) where the area inside the blue dashed circle displays the image by MIID; more discussion is provided in Sec. S3 of the Supplementary Material]. Due to the chromatic dispersion of the metalens, the focal length will be longer at shorter wavelengths, which results in a decreased NA and zoom-out imaging at a constant imaging distance. Inheriting the chromatic dispersion, this MIID is capable of acquiring the depth of objects without mechanical movement. To manifest this function, we fabricated two microscale samples on the top (side A) and bottom (side B) of a glass coverslip, as schematically shown in Fig. 3(b) (see imaging setup in Fig. S1 in the Supplementary Material). Here, characters “DSL” and “NJU” were fabricated on both sides of a coverslip by maskless lithography with a distance of 170 μm (i.e., coverslip thickness).
whole lateral sizes of the two objects are both $\sim 80 \mu m$. With a certain image distance ($\sim 500 \mu m$), we illuminate the sample with light of different wavelengths. From Fig. 3(c), a clear image of NJU but a blurred DSL image is observed at $\lambda = 660$ nm, and vice versa at $\lambda = 580$ nm. It does demonstrate the capability of DOF tuning via switching the illumination wavelength.

### 4 Wide-Field Imaging of MIID Integrated with PMDP Metalens Array

There have been several works dedicated to image aberration correction with singlet or doublet metalenses to enlarge the imaging FOV. However, an increase of the metalens size to a macroscopic size in the single axis imaging scheme will inevitably increase the working distance, which definitely weakens the ultrathin and ultralight advantages of metalenses. We prefer the MIID to work in a short-working distance in an enlarged FOV, to keep the advantage of compact integration as it is mounted to the CMOS image sensor. However, the imaging principle constrains the single lens size with very limited imaging area, which greatly prevents its practical application. To circumvent this limitation and obtain a large FOV imaging, we proposed a metalens array for MIID to acquire multiple images and stitch them together. Due to the small FOV of individual metalenses (see details in Sec. S4 of the Supplementary Material), only part of the object can be imaged, and these
images will not overlap in a 4f imaging system. Therefore, there will be blind areas as we stitch these sub-images, which prohibits constructing a complete image.

Fortunately, a powerful capability of the metasurface is the flexible design with multiplexed functions in a single device, which possibly provides a solution to make up the blind areas of the FOV. Recently, a general polarization multiplexed metasurface has been established via merging the geometric and propagation phases together to independently control phase profiles in two orthogonal polarization states, including the two circular polarization states. Here, in order to cover the blind areas among limited FOV of our MIID, we proposed a PMDP metalens design with cross phase profiles of certain lens areas to satisfy the requirements of two different focusing lenses working at left-hand circular polarization (LCP) and right-hand circular polarization (RCP), respectively, as shown in Fig. 4(a) (more details about the design of PMDP metalenses are provided in Sec. S5 of the Supplementary Material). By simply switching polarization states, we can obtain two independent images.

Figure 4(b) shows the optical microscopic image of a PMDP metalens with size of 200 μm. We arranged the metalens into a 6 × 6 array, containing 6 × 6 metalens for LCP multiplexed with 5 × 5 metalens for RCP. The entire lens region is about 1.2 mm × 1.2 mm, as shown in Fig. 4(c). Each metalens is designed at an operating wavelength of 630 nm and focal length of 250 μm. To demonstrate the advances in compact integration, we have packaged the whole imaging system into a significantly miniaturized prototype with a size about 3.5 cm × 3 cm × 2.5 cm. Figure 4(d) shows a photograph of the prototype including the LED matrix, LED controller, polarizers, sample holder, and core component of MIID. The images of the resolution test chart for LCP and RCP incident light taken from MIID with the PMDP metalens array are shown in Fig. 4(e), respectively. The image distortion caused by monochromatic aberration is observable by the naked eye, especially for objects with large feature size. Figure 4(f) shows a stitched image by combining two sets of sub-images after distortion correction and background subtraction (the detailed proceeding is provided in Sec. S6 of the Supplementary Material). The stitched image demonstrated a wide FOV area, the same as the metalens array region (1.2 mm × 1.2 mm) without losing the resolution ~1.74 μm, as shown in Fig. 4(g)]. The stitched image has some stitching artifacts such as diagonal stripes due to the uneven brightness at the center and edge of sub-images caused by vignetting. At present, the performances of our MIID are still lower than that of lensless imaging (e.g., Ref. 8) both in resolution and FOV; however, MIID provides a totally new route that holds development potential for high-speed large-FOV microscopy. Moreover, our imaging process is much simpler and timesaving (our processing time is ~4 s on a laptop, while 50 s with a desktop computer is needed in Ref. 8) compared with those sophisticated post-processing algorithms in lensless imaging and would significantly save computing resources.

As an example for application, we used this MIID to image a biospecimen of a Pap smear and dragonfly wing (as shown in Fig. 5). Compared to the optical microscopic images (Olympus, 10× objective, NA = 0.3) in the left panels of Fig. 5, the stitched images show good consistency and better contrast for these translucent or low-index-contrast biospecimens. This stitched image covers 36 times the area of a single metalens without decreasing the resolution and increasing the working distance, which is ready to expand to much larger areas until it covers the whole CMOS image sensor. Therefore, our approach does provide a successful solution to break the restriction between high resolution and wide FOV and make it feasible for high-throughput bioimaging and diagnosis.

5 Discussions and Conclusion

We have shown a metalens-integrated compact imaging device for wide-field microscopy achieved by directly mounting the metalens to an image sensor. Based on the silicon metalens working in the red light wavelength range, the imaging performances of the integrated system, including the resolution, SNR, imaging aberration, and FOV, were systematically investigated. The spectral optical zooming and DOF-resolved imaging have been achieved by taking advantage of the large dispersion of the metalens. More importantly, the metalens array with polarization multiplexing is used to reach a wide FOV imaging, which breaks the link between resolution and FOV. Finally, a miniaturized prototype is demonstrated to show the powerful capability of compact integration. Frankly, the performance of the current MIID is not good enough compared with conventional microscope and some of the computational imaging devices. In addition to the stitching artifacts that can be further improved by optimization, the relatively low working efficiency of the metalens would mainly account for background noises and restricted imaging performance. Fortunately, there are still opportunities in improving the efficiency of metalenses by adopting low-loss materials (e.g., GaN and SiN) and higher aspect-ratio nano-post elements. Moreover, future development of smaller pixels of the CMOS sensor will also enhance the MIID capability for higher resolutions. Our approach provides a new solution of ultra-compact and wide-field imaging by taking advantage of metasurfaces, which may inspire more revolutionary compact optical devices.
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References

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